

Abstract**Voltage-offset diode**

The interface device consists of a voltage offset diode (DD) constructed using monolithic microwave integrated technology, mounted between the output (S) of the upstream circuit (16) and the input of the downstream circuit (18). The characteristic of the offset diode (DD) is selected such that the bias voltage (VD) of the upstream circuit (16) is offset by an offset corresponding more or less to the disparity between the bias voltages (VD and VL) of the upstream (16) and downstream (8) circuits. The bias current of the downstream circuit is relatively high in comparison with the threshold current of the offset diode.

Figure 3.